LITE ON SEMICONDUCTOR

MCR100-6



MAXIMUM RATINGS (Tj= 25°C unless otherwise noticed)

Rating	Symbol	Value	Unit	
Peak Repetitive Off – State Voltage (TJ= -40 to 110 $^\circ$ C, Sine Wave, 50 to 60 Hz; Gate Open)	Vdrm vrrm	400	Volts	
On-State RMS Current (Tc = 80 $^{\circ}$ C) 180 $^{\circ}$ Conduction Angles	IT(RMS)	0.8	Amps	
Peak Non-Repetitive Surge Current (1/2 Cycle, Sine Wave, 60 Hz, TJ = 25° C)	Ітѕм	10	Amps	
Circuit Fusing Consideration (t = 8.3 ms)	l ² t	0.415	A ² s	
Forward Peak Gate Power (Ta = 25 $^\circ\!$ C, Pulse Width \leq 1.0 us)	Рсм	0.1	Watts	
Forward Average Gate Power (Ta = $25^{\circ}C$, t = 8.3 ms)	PG(AV)	0.1	Watts	
Forward Peak Gate Current (Ta = 25°C, Pulse Width≦1.0 us)	lgм	1	Amps	
Reverse Peak Gate Voltage (Ta = 25 $^{\circ}$ C, Pulse Width \leq 1.0 ms)	Vgrm	5	Volts	
Operating Junction Temperature Range @ Rate VRRM and VDRM	TJ	-40 to + 110	°C	
Storage Temperature Range	Tstg	-40 to + 150	°C	
		REV. 1, Oct-2010, 1	TXD24	



THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance – Junction to Case	RthjC	75	°C/W
Maximum Lead Temperature for Soldering Purposes 1/16" from Case for 10 Seconds	ΤL	260	°C

ELECTRICAL CHARACTERISTICS (Tj= 25°C unless otherwise noticed)

Characteristic	Symbol	Min	Тур	Мах	Unit

OFF CHARACTERSITICS

Peak Reptitive Forward or Reverse Blocking Current $T_J=25^{\circ}C$ IDRM10(VD=Rated VDRM and VRRM; RGK =1K Ohms) $T_J=110^{\circ}C$ IRRM100
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ON CHARACTERISTICS

Peak Forward On-State Voltage (ITM= \pm 1.6A Peak, Pulse Width \leq 1.0ms, Duty Cycle \leq 1%)	VTM	 	1.7	Volts	
Gate Trigger Current(VD= 7.0 Vdc, RL=100 Ohms) (1)	IGT	 	50	uA	
Holding Current(VD= 7.0 Vdc, Intitiating Current = 20mA)	TJ= 25 ℃	lн	 	5	mA
Toking Curren(VD- 7.0 Vdc, mulaling Current - 2011A)	TJ= -40 ℃		 	10	
Gate Trigger Voltage(VD= 7.0 Vdc, RL=100 Ohms) (1)	TJ= 25℃	VGT	 	0.8	Volts
	TJ= -40 ℃		 	1.2	
Latch Current(VD= 7.0 Vdc, RL 100 Ohms)	TJ= 25℃	۱L	 	10	mA
	TJ= -40°℃		 	15	ШA

DYNAMIC CHARACTERISITCS

Critical Rate of Rise of Off-State Voltage (VD=Rated VDRM, Exponential Waveform, PGK=1K Ohms, TJ=110°C	dv/dt	20			V/us	
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(1) RGK current is not included in measurement



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+ Voltage



+ Current

						↑ 1	Anode +
Symbol	Parameter]		<-V _{TM}	
V _{DRM}	Peak Repetitive	Off State Fo	rward Voltage	-		-	
IDRM	Peak Forward E				on state ´		
V _{RRM}	Peak Repetitive			I _{RRM} at V	RRM	<u> </u>	
I _{RRM}	Peak Reverse E	Blocking Curre	ent				
V _{TM}	Peak on State \						
I _H	Holding Current	t			T Biocking Region		_{DRM} at V _{DRM}
					(off state)	Forward Bloc	
					Aveleneke Desien	(off st	
					Avalanche Region	L `	,
				Anode –		V	
				VTM -	IT		
	10						-
	_						
	ate						
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	2 2						
	S C						
	sdw sno						
	aeous c t(Amps L						
	intaeous c ent(Amps L						
	istantaeous c :urrent(Amps L						
	, Instantaeous o current(Amps) L					-Tj=110°C	
	(A), Instantaeous c current(Amps L					-	
	IT(A), Instantaeous on-state current(Amps) J					- Tj=110℃	
	IT(A), Instantaeous c current(Amps 1					-	

VT, Instantaneous on-state voltage(Volts)

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Figure 1. On-State Characteristics

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